

High-Temperature Silicon Carbide (SiC) Half-Bridge Power Module

TMOS Version

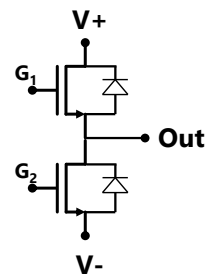
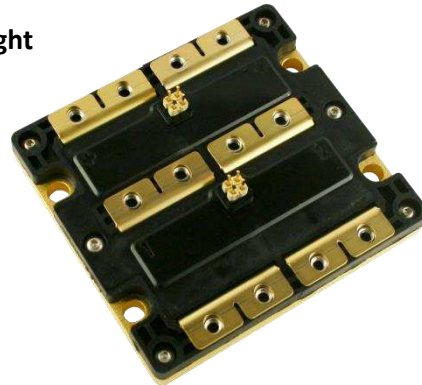
FEATURES

- High temperature: $T_{c(max)} = 225\text{ }^{\circ}\text{C}$
 $T_{j(max)} = 225\text{ }^{\circ}\text{C}$
- AS9100:Rev. C-certified manufacturing, traceable throughout value chain
- Ultra-fast switching (<30 ns), low inductance
- High system efficiency
- Flux-free, void-free packaging
- Low profile, small form factor, extremely lightweight
- High reliability

600 V / 1000 A / 1.4 m Ω

APPLICATIONS

- High-efficiency converters / inverters
- Motor drives
- Aerospace: Military & Commercial
- Smart grid/grid-tie distributed generation



DESCRIPTION

The APE HT-2201 Silicon Carbide (SiC) half-bridge power module was designed specifically to address the growing demand for higher power densities, higher temperatures, and higher switching frequencies.

COMPANION PARTS

Maximum performance may be obtained through use of the companion high-temperature gate driver, part number APE MTGD2-2011, designed especially for driving the Silicon Carbide module.

Power Module Absolute Maximum Ratings ($T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Condition(s) | Value | Units |
|--------------|--|--|-------------|------------------|
| V_{DSS} | Drain-source voltage | | 600 | V |
| V_{GSS} | Gate-source voltage | | -5 to 20 | V |
| I_D | Continuous drain current | $T_c = 25\text{ }^\circ\text{C}$ | 1000 | A |
| | | $T_c = 100\text{ }^\circ\text{C}$ | TBD | |
| | | $T_c = 225\text{ }^\circ\text{C}$ | TBD | |
| I_{DM} | Peak pulsed drain current | Pulse width $\leq 10\text{ }\mu\text{s}$, duty cycle $\leq 2\%$ | TBD | A |
| P_D | Maximum power dissipated | | 1600 | W |
| $T_{c(max)}$ | Maximum case temperature ¹ | | 225 | $^\circ\text{C}$ |
| $T_{j(min)}$ | Minimum operating junction temperature | | - 50 | $^\circ\text{C}$ |
| $T_{j(max)}$ | Maximum operating junction temperature | | 225 | |
| T_{stg} | Storage temperature | | - 50 to 225 | $^\circ\text{C}$ |
| V_{isol} | Insulation test voltage | AC, 1 min. | TBD | V |
| | | AC, 1 s. | TBD | |

Power Module Switch Position Electrical Characteristics ($T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Symbols | Parameter | Condition(s) | Values | | | Units |
|---------------|---------------------------------|---|--------|---------|------|---------------|
| | | | Min. | Typical | Max. | |
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = -2\text{ V}$, $I_D = 1\text{ mA}$ | 600 | - | - | V |
| $V_{GS(th)}$ | Gate-source threshold voltage | $V_{DS} = 10\text{ V}$, $I_D = 1\text{ mA}$ | 1.0 | - | 3.0 | V |
| | | $V_{DS} = V_{GS}$, $I_D = 1\text{ mA}$, $T_j = 200\text{ }^\circ\text{C}$ | TBD | - | TBD | |
| I_{DSS} | Drain-source leakage current | $V_{GS} = -2\text{ V}$, $V_{DS} = 600\text{ V}$ | - | - | 200 | μA |
| | | $V_{GS} = 2\text{ V}$, $V_{DS} = 600\text{ V}$, $T_j = 200\text{ }^\circ\text{C}$ | - | - | TBD | |
| I_{GSS} | Gate-source leakage current | $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$ | - | - | 40 | μA |
| $R_{DS(on)}$ | Drain-source turn-on resistance | $V_{GS} = 20\text{ V}$, $I_D = 1000\text{ A}$ | - | 1.4 | 1.6 | m Ω |
| | | $V_{GS} = 20\text{ V}$, $I_D = 1000\text{ A}$, $T_j = 150\text{ }^\circ\text{C}$ | - | TBD | TBD | |
| C_{iss} | Input capacitance | $V_{GS} = 0\text{ V}$ | - | TBD | - | pF |
| C_{oss} | Output capacitance | $V_{DS} = 600\text{ V}$ | - | TBD | - | |
| C_{rss} | Reverse transfer capacitance | $f = 1\text{ MHz}$ | - | TBD | - | |
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 200\text{ V}$, $V_{GS} = -4\text{ to }20\text{ V}$ $I_D = 500\text{ A}$ $R_{G(ext)} = 1.0\text{ }\Omega$, $R_L = 43\text{ }\mu\text{H}$ | - | TBD | - | ns |
| t_{rv} | Rise time | | - | 45 | - | |
| $t_{d(off)}$ | Turn-off delay time | | - | TBD | - | |
| t_{fv} | Fall time | | - | 35 | - | |

¹The packaging materials have been qualified at this temperature.

Power Module Switch Position Gate Charge Electrical Characteristics ($T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Symbols | Parameter | Condition(s) | Values | | | Units |
|----------|-----------------------|--|--------|---------|------|-------|
| | | | Min. | Typical | Max. | |
| Q_{gs} | Gate to source charge | $V_{DD} = 400\text{ V}$, $V_{GS} = -4\text{ to }20\text{ V}$ $I_D = 1000\text{ A}$ $R_{G(ext)} = xx\ \Omega$, $R_L = xx\ \Omega$ | TBD | - | - | nC |
| Q_{gd} | Gate to drain charge | | TBD | - | - | |
| Q_g | Gate charge total | | TBD | - | - | |

Power Module Diode Position Electrical Characteristics ($T_c = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Symbols | Parameter | Condition(s) | Values | | | Units |
|----------|-------------------|--|--------|---------|------|---------------|
| | | | Min. | Typical | Max. | |
| V_{FM} | Forward voltage | $I_F = 50\text{ A}$ | - | 3.4 | - | V |
| | | $I_F = 300\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$ | - | 5.3 | - | |
| I_R | Reverse current | $V_R = 600\text{ V}$ | - | TBD | - | μA |
| | | $V_R = 600\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ | - | TBD | - | |
| Q_C | Capacitive charge | $V_R = 600\text{ V}$, $I_F = 450\text{ A}$, $di/dt = 22900\text{ A}/\mu\text{s}$ | - | TBD | - | nC |

Power Module Thermal Characteristics² ($T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Symbols | Parameter | Condition(s) | Values | | | Units |
|-------------------|--------------------------------------|--------------|--------|---------|------|---------------------------|
| | | | Min. | Typical | Max. | |
| $R_{\theta(j-c)}$ | FET thermal resistance junction-case | | | 0.125 | | $^\circ\text{C}/\text{W}$ |

Power Module Mechanical Characteristics ($T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified)

| Symbols | Parameter | Condition(s) | Values | | | Units |
|---------|----------------------------|--|--------|---------|------|-------|
| | | | Min. | Typical | Max. | |
| w | Weight | | | 140 | | g |
| M_s | Lead frame mounting torque | 6-32 steel screw for lead frame, 10-32 steel screw for baseplate | | 40 | | in-lb |

TYPICAL PERFORMANCE CURVES

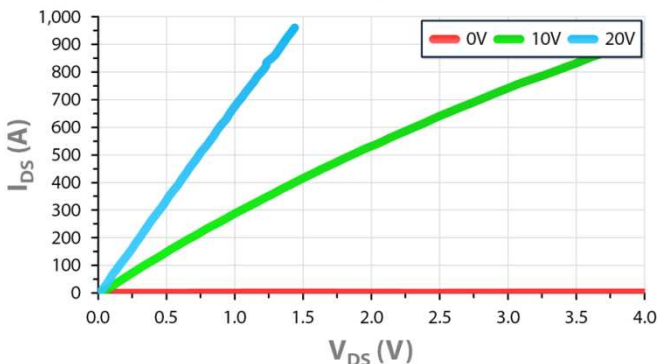
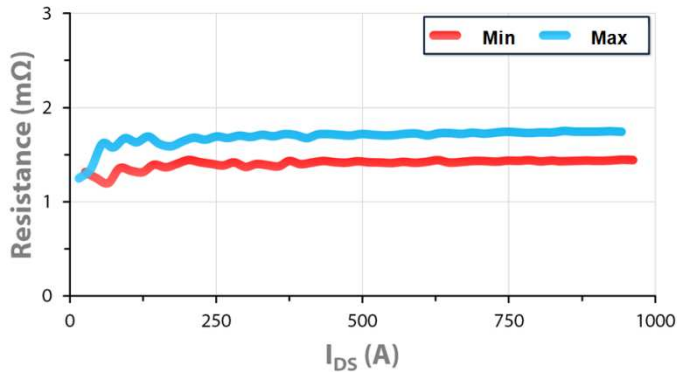
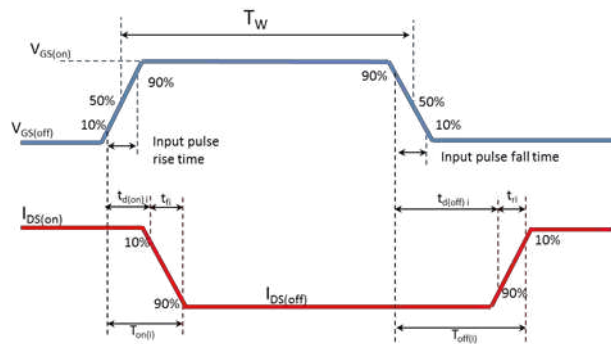
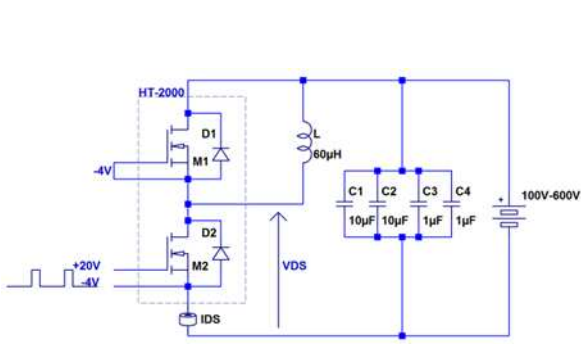
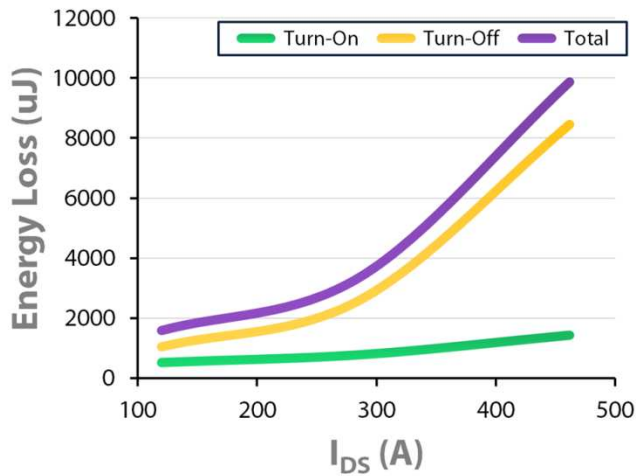


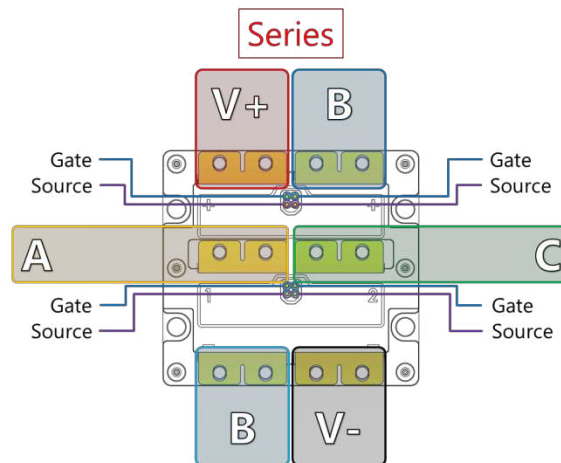
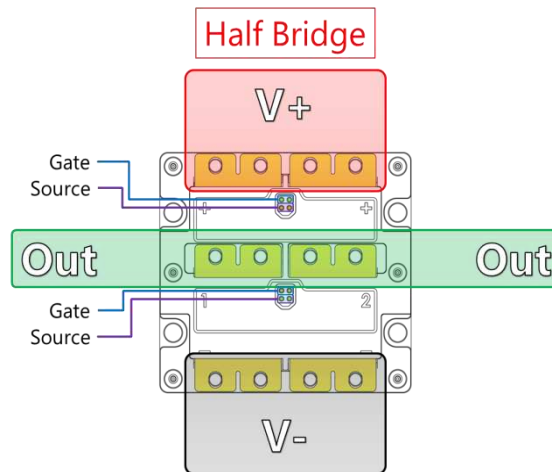
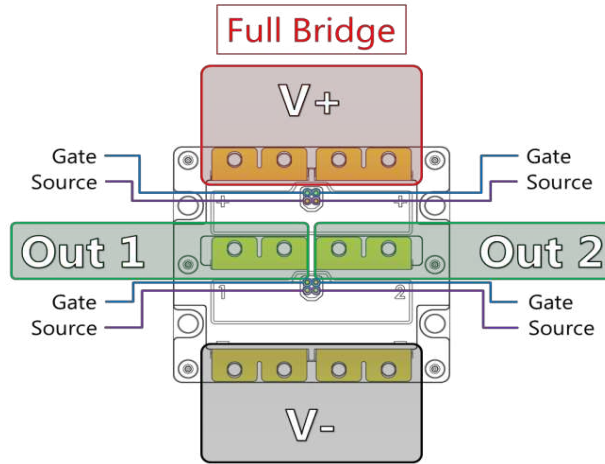
Fig. 1 - Die Junction @ 25 °C

² FET thermal resistance junction-case is calculated measured with a 105 °C coldplate and full power distributed through the FETs. The thermal properties typically improve at lower temperatures.



Typical Normalized On Resistance

 Normalized to an on resistance value of 1.4 mΩ ($I_D = 1000\text{ A}$, $T_j = 25\text{ °C}$)

Typical Switching Losses

 Energy values obtained using companion gate driver ($T_{amb} = 25\text{ °C}$).



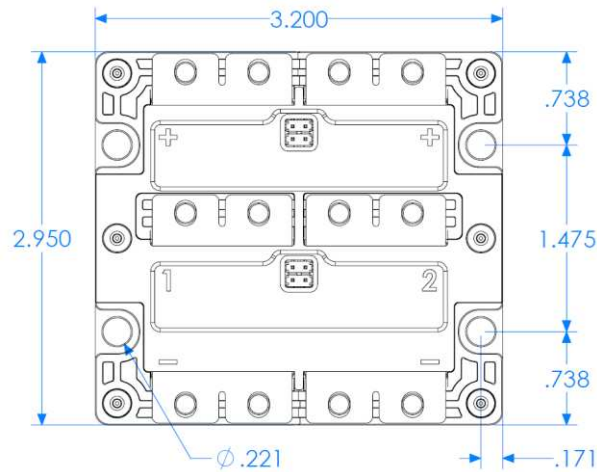
MOUNTING DIMENSIONS

All dimensions are listed in inches

#10-32 bolts are recommended for mounting

A torque of 40 in·lb is recommended

CAD models are available upon request



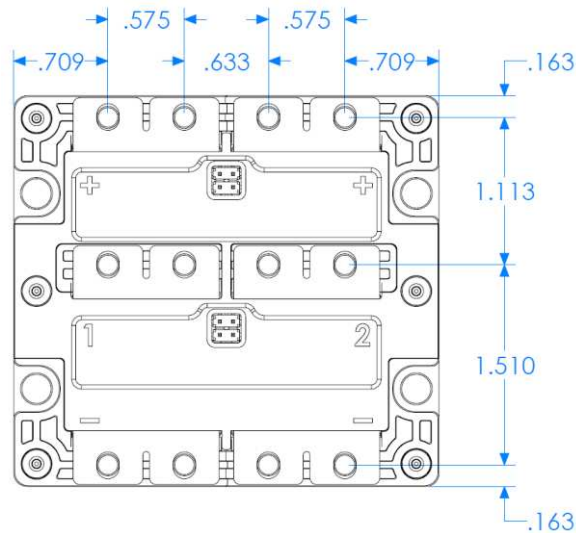
POWER CONTACT DIMENSIONS

All dimensions are listed in inches

#6-32 bolts required for the power contacts

A torque of 40 in·lb is recommended

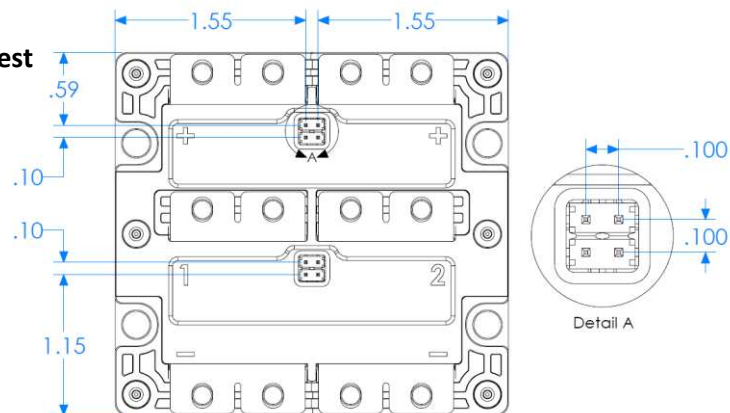
CAD models are available upon request



GATE DRIVE CONNECTIONS

All dimensions are listed in inches

CAD models are available upon request





PRELIMINARY

APE HT-2103

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